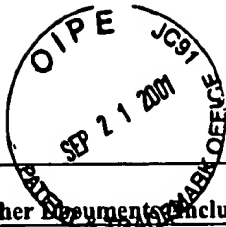
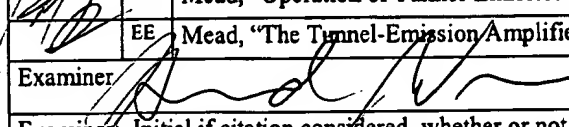




Form PTO 1449 (Rev. 2-32)				U.S. Department of Commerce Patent and Trademark Office		Atty. Docket No. CAY-006		Serial No. 09/943,338	
Information Disclosure Statement by Applicant						Applicant: John M. Caywood			
(Use several sheets if necessary)						Filed: 8/28/2001 Group: (to be assigned) 2819			
U.S. Patent Documents									
Init.		Document No.	Date	Name	Class	Subclass	Filing Date		
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BB	Krolikowski, "Photoemission Studies of the Noble Metals. I. Copper", <i>Physical Review</i> , Vol. 185, No. 3, pp. 882-900 (1969)	
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Examiner 		Date Considered 9/31/04
Examiner: Initial if citation considered, whether or not citation is in conformance with MPEP 609; Draw line through citation if not in conformance and not considered. Include a copy of this form with the next communication to applicant.		